

UHV study of hydrogen atom induced etching of amorphous hydrogenated silicon thin films

Zechcjf T, Brandnei BD, Biener J, Küppers J.
The journal of physical chemistry. B
2001; 105(17):3502-3509

ARTICLE IDENTIFIERS

DOI: 10.1021/jp0022611
PMID: unavailable
PMCID: not available

JOURNAL IDENTIFIERS

LCCN: 98660822
pISSN: 1520-6106
eISSN: 1520-5207
OCLC ID: 37604309
CONS ID: sn 97034879
US National Library of Medicine ID: 101157530

This article was identified from a query of the SafetyLit database.